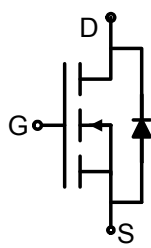
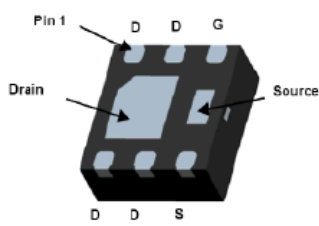


N-Channel Enhancement Mode Power MOSFET

<p><b>Description</b> The HM2300DR uses advanced trench technology to provide excellent <math>R_{DS(ON)}</math>, low gate charge and operation with gate voltages as low as 2.5V. This device is suitable for use as a battery protection or in other switching application.</p> <p><b>General Features</b></p> <ul style="list-style-type: none"> <li>● <math>V_{DS} = 20V, I_D = 8.0A</math></li> <li>● <math>R_{DS(ON)} &lt; 40m\Omega @ V_{GS}=2.5V</math></li> <li>● <math>R_{DS(ON)} &lt; 33m\Omega @ V_{GS}=4.5V</math></li> <li>● High power and current handling capability</li> <li>● Lead free product is acquired</li> <li>● Surface mount package</li> </ul> <p><b>Application</b></p> <ul style="list-style-type: none"> <li>● Battery protection</li> <li>● Load switch</li> <li>● Power management</li> </ul>	<div style="text-align: center;">  <p><b>Schematic diagram</b></p> </div> <div style="text-align: center; margin-top: 20px;">  <p><b>DFN2X2-6L bottom view</b></p> </div>
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**Package Marking and Ordering Information**

Device Marking	Device	Device Package	Reel Size	Tape width	Quantity
2300	HM2300DR	DFN2X2-6L	Ø180mm	8 mm	3000 units

**Absolute Maximum Ratings ( $T_A=25^\circ C$  unless otherwise noted)**

Parameter	Symbol	Limit	Unit
Drain-Source Voltage	$V_{DS}$	20	V
Gate-Source Voltage	$V_{GS}$	$\pm 12$	V
Continuous Drain Current	$I_D$	$T_A = 25^\circ C$	8.0
		$T_A = 70^\circ C$	6.4
Drain Current-Pulsed (Note 1)	$I_{DM}$	32	A
Maximum Power Dissipation	$P_D$	6.8	W
Operating Junction and Storage Temperature Range	$T_J, T_{STG}$	-55 To 150	$^\circ C$

**Thermal Characteristic**

Thermal Resistance, Junction-to-Ambient (Note 2)	$R_{\theta JA}$	100	$^\circ C/W$
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**Electrical Characteristics ( $T_A=25^\circ C$  unless otherwise noted)**

Parameter	Symbol	Condition	Min	Typ	Max	Unit
<b>Off Characteristics</b>						
Drain-Source Breakdown Voltage	$BV_{DSS}$	$V_{GS}=0V, I_D=250\mu A$	20	22	-	V

Zero Gate Voltage Drain Current	$I_{DSS}$	$V_{DS}=20V, V_{GS}=0V$	-	-	1	$\mu A$
Gate-Body Leakage Current	$I_{GSS}$	$V_{GS}=\pm 12V, V_{DS}=0V$	-	-	$\pm 100$	nA
<b>On Characteristics (Note 3)</b>						
Gate Threshold Voltage	$V_{GS(th)}$	$V_{DS}=V_{GS}, I_D=250\mu A$	0.5	0.65	1.2	V
Drain-Source On-State Resistance	$R_{DS(on)}$	$V_{GS}=2.5V, I_D=4.0 A$	-	33	40	m $\Omega$
		$V_{GS}=4.5V, I_D=4.5A$	-	22	33	m $\Omega$
Forward Transconductance	$g_{FS}$	$V_{DS}=10V, I_D=4A$	-	10	-	S
<b>Dynamic Characteristics (Note4)</b>						
Input Capacitance	$C_{iss}$	$V_{DS}=8V, V_{GS}=0V,$ $F=1.0MHz$	-	500	-	PF
Output Capacitance	$C_{oss}$		-	300	-	PF
Reverse Transfer Capacitance	$C_{rss}$		-	140	-	PF
<b>Switching Characteristics (Note 4)</b>						
Turn-on Delay Time	$t_{d(on)}$	$V_{DD}=10V, I_D=1A$ $V_{GS}=4.5V, R_{GEN}=6\Omega$	-	20	40	nS
Turn-on Rise Time	$t_r$		-	18	40	nS
Turn-Off Delay Time	$t_{d(off)}$		-	60	108	nS
Turn-Off Fall Time	$t_f$		-	28	56	nS
Total Gate Charge	$Q_g$	$V_{DS}=10V, I_D=3A, V_{GS}=4.5V$	-	10	15	nC
Gate-Source Charge	$Q_{gs}$		-	2.3	-	nC
Gate-Drain Charge	$Q_{gd}$		-	2.9	-	nC
<b>Drain-Source Diode Characteristics</b>						
Diode Forward Voltage (Note 3)	$V_{SD}$	$V_{GS}=0V, I_S=1A$	-	-	1.2	V
Diode Forward Current (Note 2)	$I_S$		-	-	1	A

**Notes:**

1. Repetitive rating: pulse width limited by maximum junction temperature.
2. Surface mounted on FR4 Board,  $t \leq 10$  sec.
3. Pulse test: pulse width  $\leq 300\mu s$ , duty cycle  $\leq 2\%$ .
4. Guaranteed by design, not subject to production

Typical Electrical and Thermal Characteristics

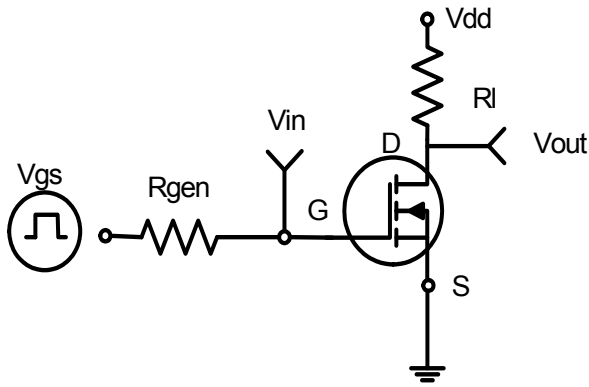


Figure 1: Switching Test Circuit

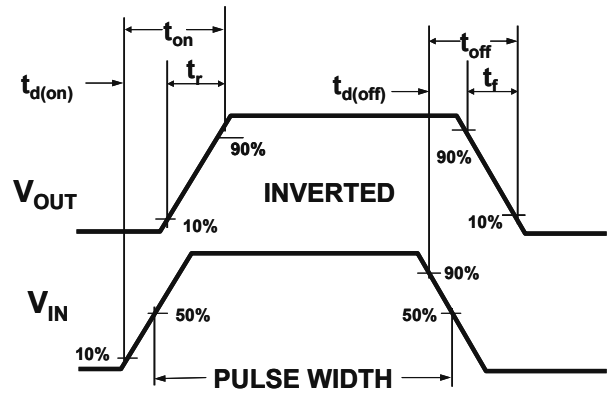


Figure 2: Switching Waveforms

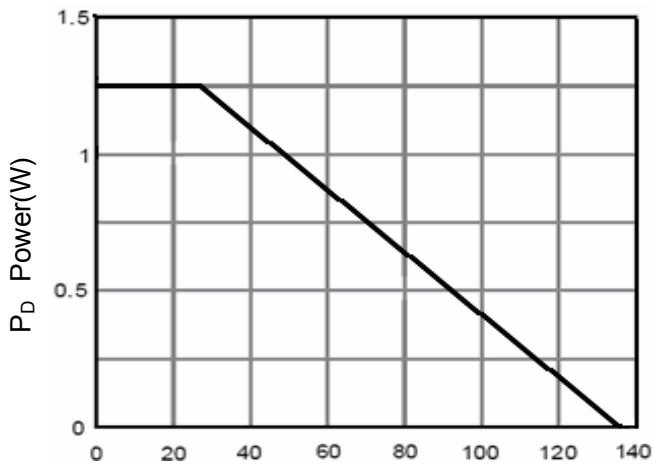


Figure 3 Power Dissipation

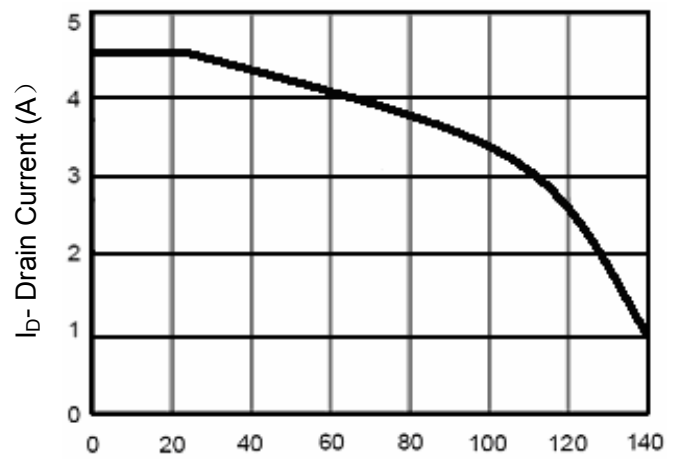


Figure 4 Drain Current

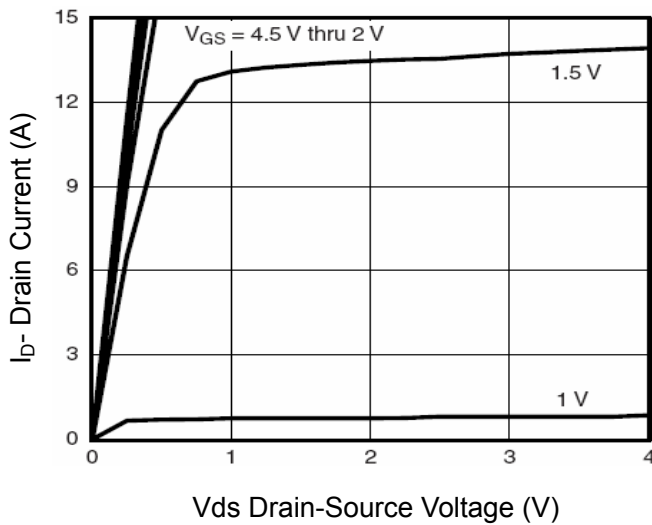


Figure 5 Output CHARACTERISTICS

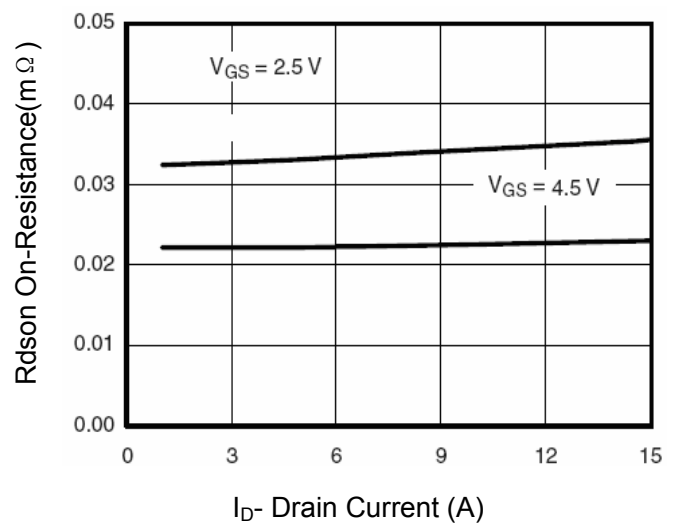
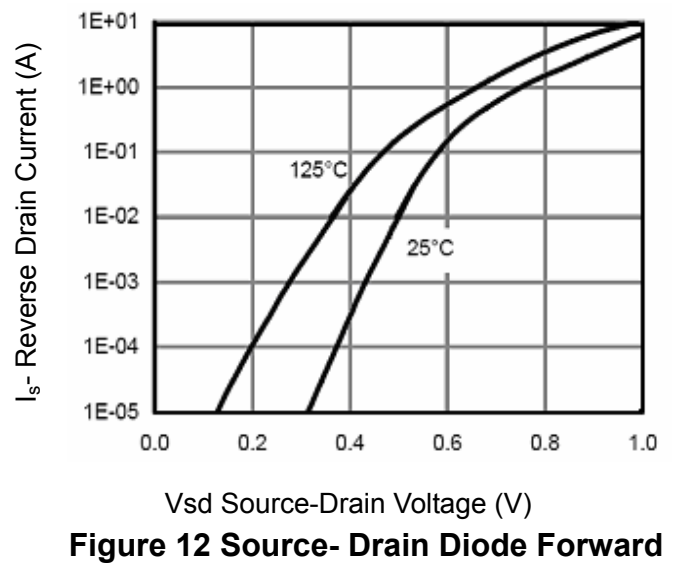
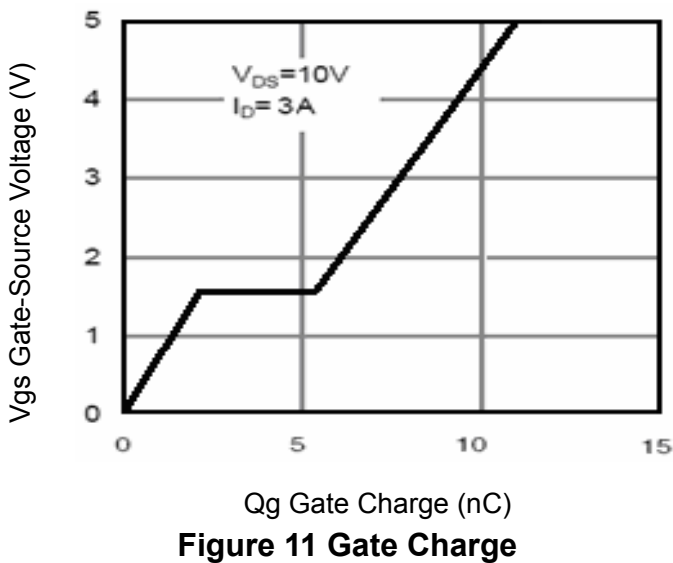
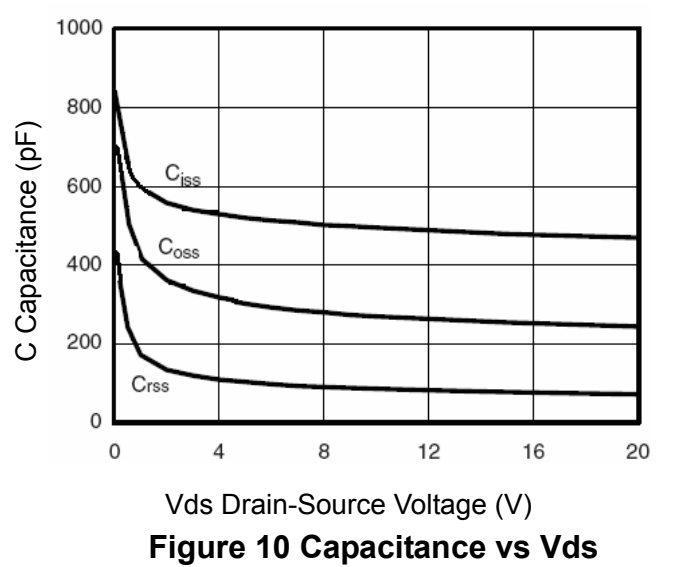
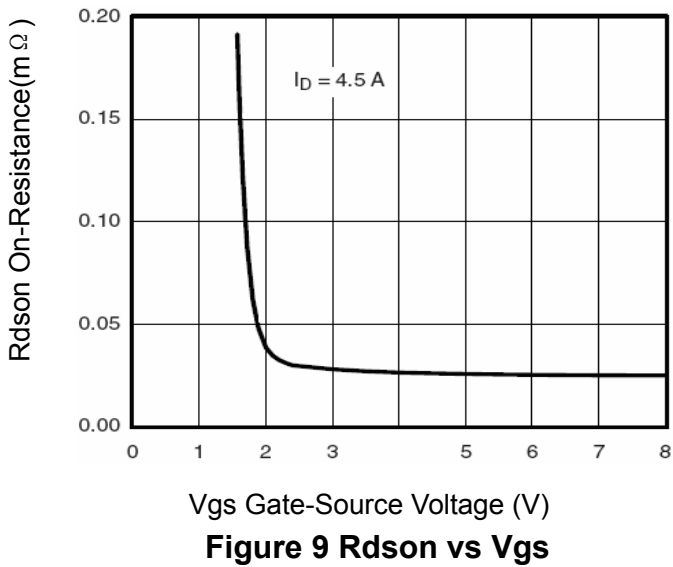
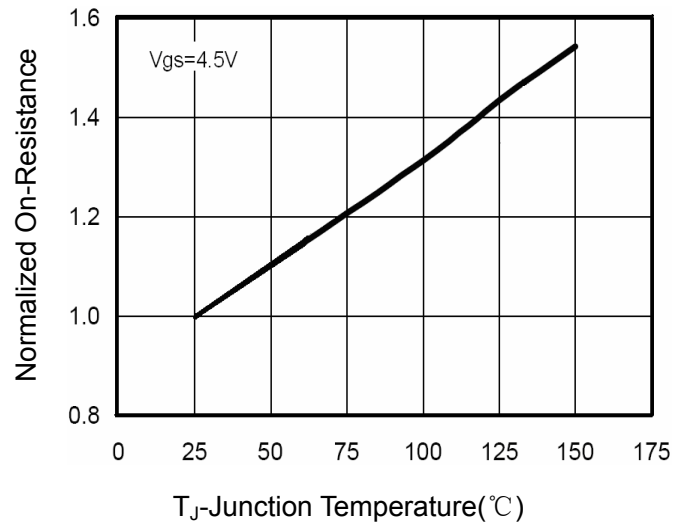
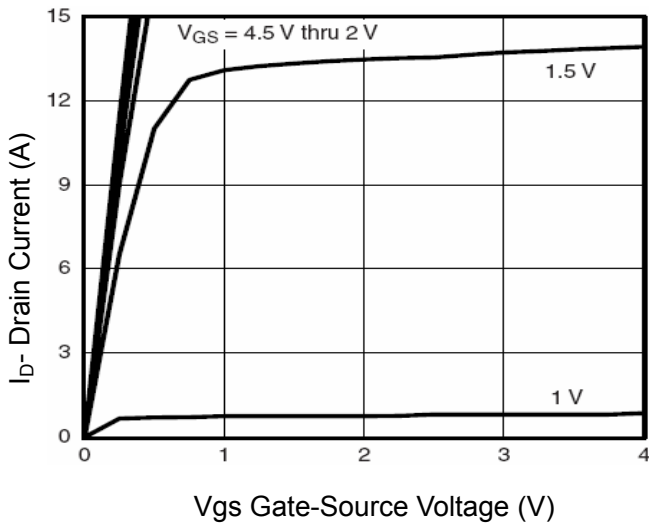


Figure 6 Drain-Source On-Resistance



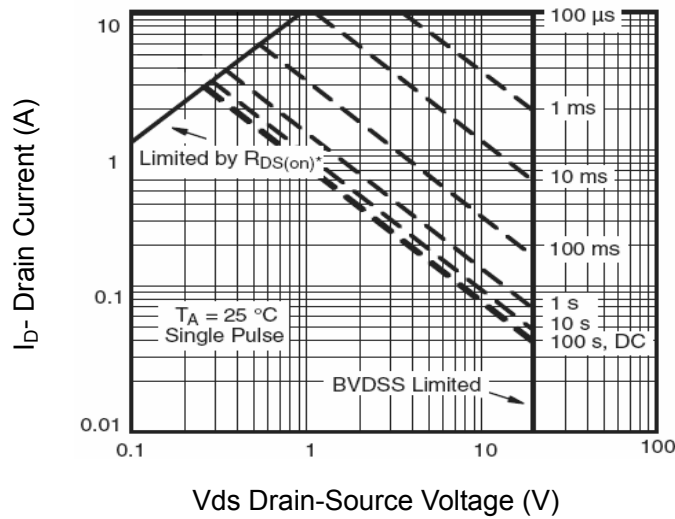


Figure 13 Safe Operation Area

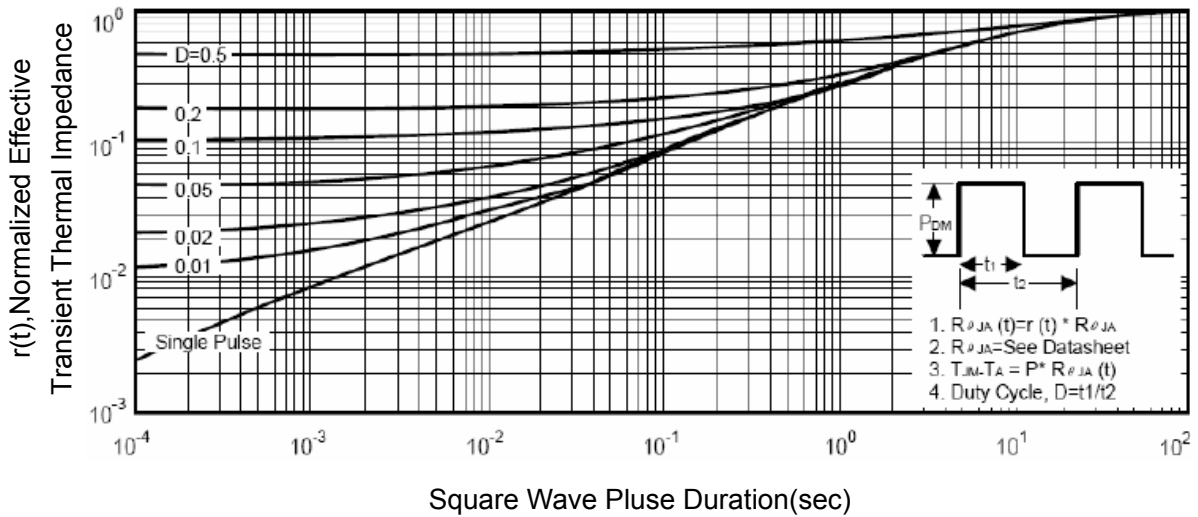
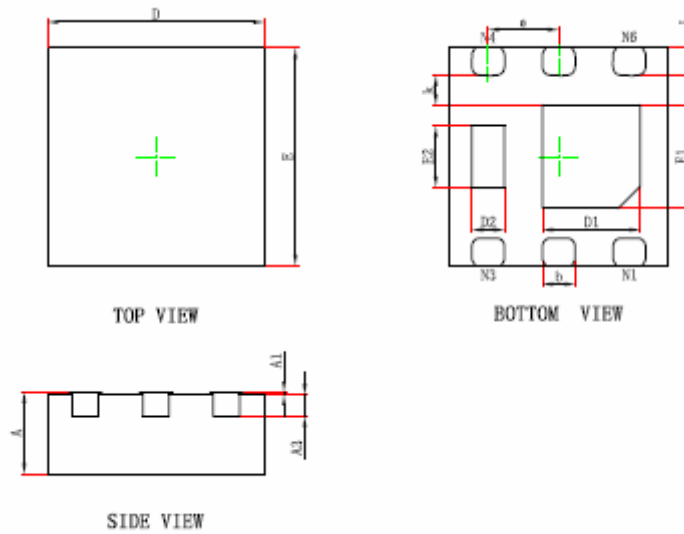


Figure 14 Normalized Maximum Transient Thermal Impedance

DFN2X2-6L Package Information



Symbol	Dimensions In Millimeters		Dimensions In Inches	
	Min.	Max.	Min.	Max.
A	0.700	0.800	0.028	0.031
A1	0.000	0.050	0.000	0.002
A3	0.203REF.		0.008REF.	
D	1.924	2.076	0.076	0.082
E	1.924	2.076	0.076	0.082
D1	0.800	1.000	0.031	0.039
E1	0.850	1.050	0.033	0.041
D2	0.200	0.400	0.008	0.016
E2	0.460	0.660	0.018	0.026
k	0.200MIN.		0.008MIN.	
b	0.250	0.350	0.010	0.014
e	0.650TYP.		0.026TYP.	
L	0.174	0.326	0.007	0.013

Notes

1. All dimensions are in millimeters.
2. Tolerance  $\pm 0.10\text{mm}$  (4 mil) unless otherwise specified
3. Package body sizes exclude mold flash and gate burrs. Mold flash at the non-lead sides should be less than 5 mils.
4. Dimension L is measured in gauge plane.
5. Controlling dimension is millimeter, converted inch dimensions are not necessarily exact.

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